



# ST2001FX

## HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

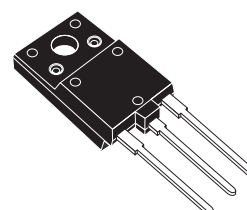
- NEW SERIES, ENHANCED PERFORMANCE
- FULLY INSULATED PACKAGE (U.L. COMPLIANT) FOR EASY MOUNTING
- HIGH VOLTAGE CAPABILITY
- HIGH SWITCHING SPEED
- TIGHTER  $h_{fe}$  CONTROL
- IMPROVED RUGGEDNESS

### APPLICATIONS:

- HORIZONTAL DEFLECTION FOR COLOR TVS OVER 21 INCHES AND 15 INCHES MONITORS

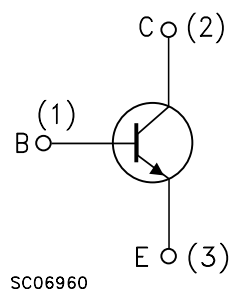
### DESCRIPTION

The device is manufactured using Diffused Collector technology for more stable operation Vs base drive circuit variations resulting in very low worst case dissipation.



ISOWATT218FX

### INTERNAL SCHEMATIC DIAGRAM



### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage ( $I_E = 0$ )	1500	V
$V_{CEO}$	Collector-Emitter Voltage ( $I_B = 0$ )	600	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	7	V
$I_C$	Collector Current	10	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	20	A
$I_B$	Base Current	7	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	63	W
$V_{ins}$	Insulation Withstand Voltage (RMS) from All Three Leads to External Heatsink	2500	V
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

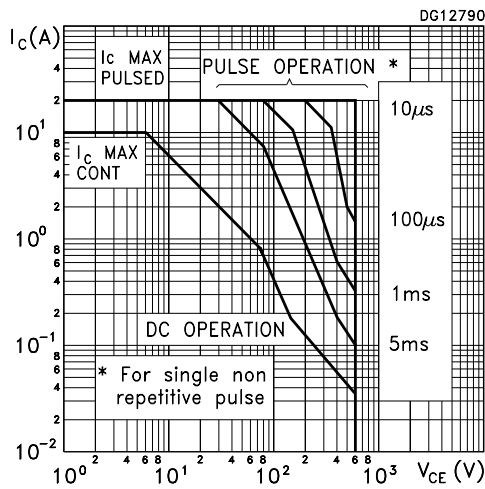
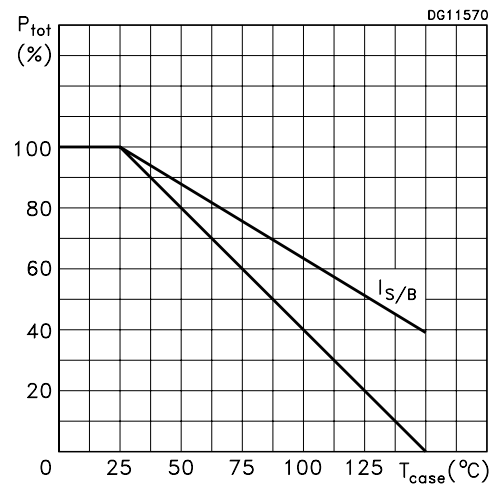
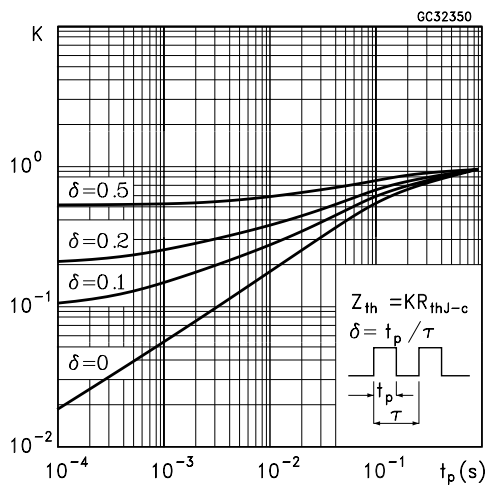
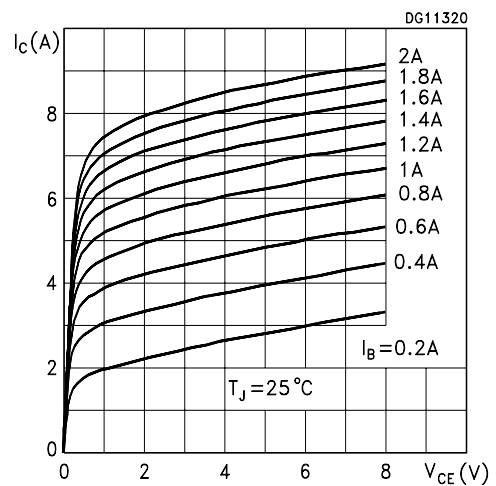
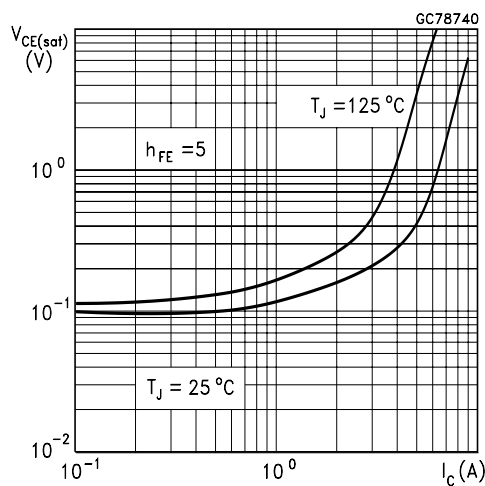
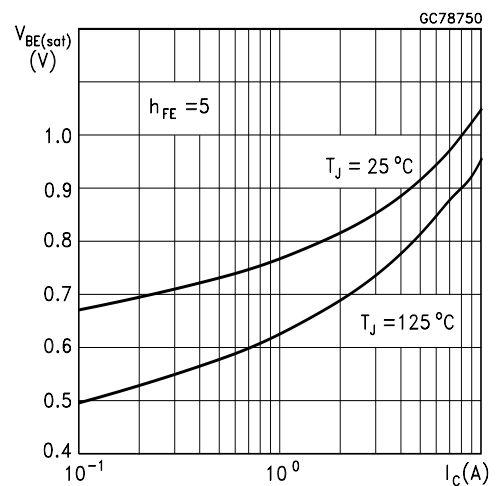
**ST2001FX****THERMAL DATA**

$R_{thj-case}$	Thermal Resistance Junction-case	Max	2	°C/W
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**ELECTRICAL CHARACTERISTICS** ( $T_j = 25\text{ °C}$  unless otherwise specified)

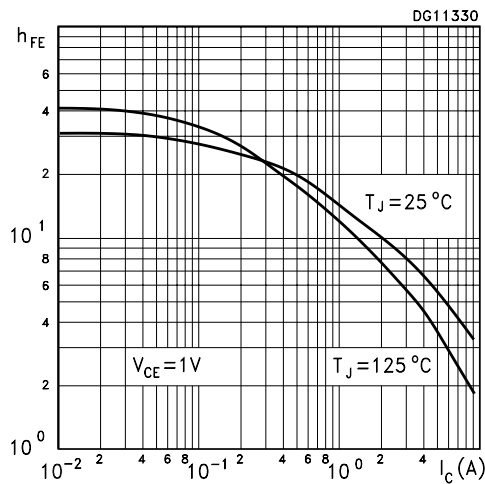
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CES}$	Collector Cut-off Current ( $V_{BE} = 0$ )	$V_{CE} = 1500\text{ V}$ $V_{CE} = 1500\text{ V}$ $T_j = 125\text{ °C}$			1 2	mA mA
$I_{EBO}$	Emitter Cut-off Current ( $I_C = 0$ )	$V_{EB} = 7\text{ V}$			1	mA
$V_{CEO(sus)}^*$	Collector-Emitter Sustaining Voltage ( $I_B = 0$ )	$I_C = 100\text{ mA}$	600			V
$V_{CE(sat)}^*$	Collector-Emitter Saturation Voltage	$I_C = 5\text{ A}$ $I_B = 1.25\text{ A}$			1.5	V
$V_{BE(sat)}^*$	Base-Emitter Saturation Voltage	$I_C = 5\text{ A}$ $I_B = 1.25\text{ A}$			1.2	V
$h_{FE}^*$	DC Current Gain	$I_C = 6\text{ A}$ $V_{CE} = 1\text{ V}$ $I_C = 6\text{ A}$ $V_{CE} = 5\text{ V}$	5	4.5	9	
$t_s$ $t_f$	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 5\text{ A}$ $V_{BB(off)} = -2.5\text{ V}$ $I_{Bon(END)} = 850\text{ mA}$ $f_h = 64\text{ KHz}$ $L_{BB(off)} = 2\text{ }\mu\text{H}$ (See Figure 1)		2.6 0.2	3 0.4	$\mu\text{s}$ $\mu\text{s}$

\* Pulsed: Pulse duration = 300  $\mu\text{s}$ , duty cycle = 1.5 %.

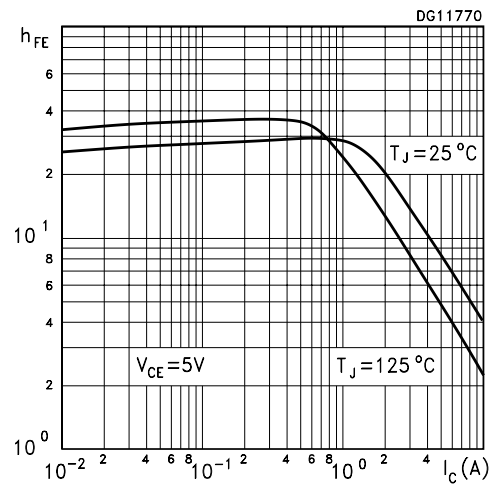
**ST2001FX****Safe Operating Area****Derating Curve****Thermal Impedance****Output Characteristics****Collector-Emitter Saturation Voltage****Base-Emitter Saturation Voltage**

## ST2001FX

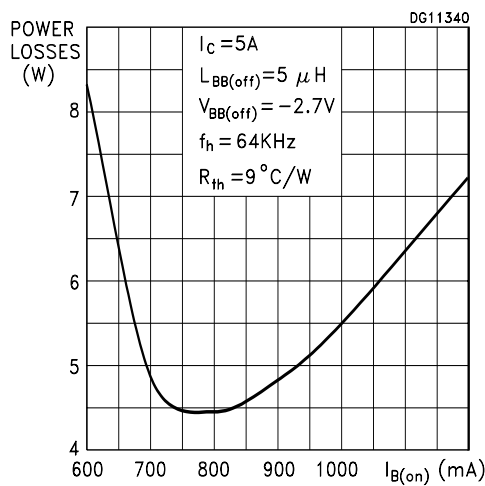
### DC Current Gain



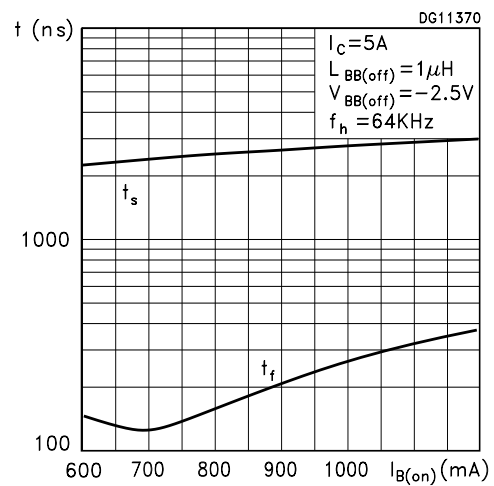
### DC Current Gain



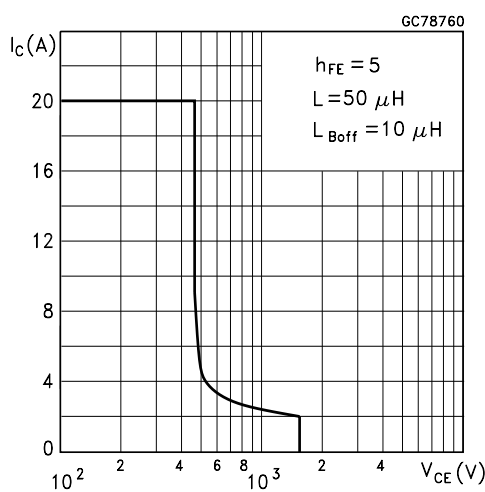
### Power Losses

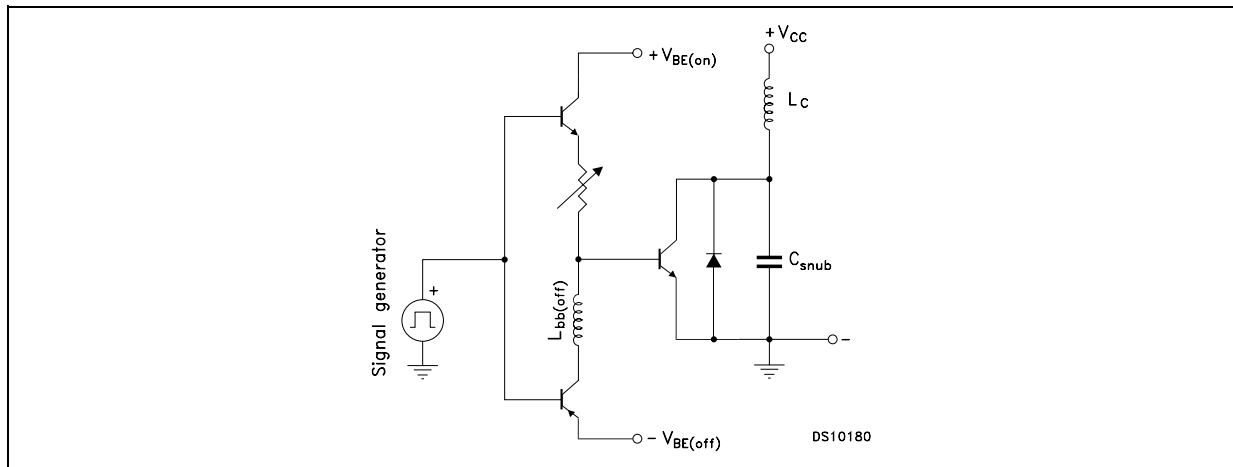


### Inductive Load Switchin Times



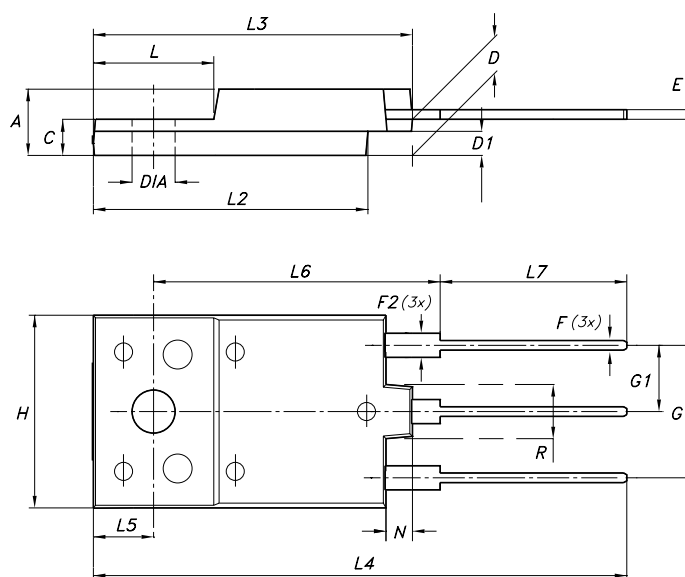
### Reverse Biased Safe Operating Area



**ST2001FX****Figure 1:** Inductive Load Switching Test Circuit

**ST2001FX****ISOWATT218FX MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	5.30		5.70	0.209		0.224
C	2.80		3.20	0.110		0.126
D	3.10		3.50	0.122		0.138
D1	1.80		2.20	0.071		0.087
E	0.80		1.10	0.031		0.043
F	0.65		0.95	0.026		0.037
F2	1.80		2.20	0.071		0.087
G	10.30		11.50	0.406		0.453
G1		5.45			0.215	
H	15.30		15.70	0.602		0.618
L	9.80		10.20	0.386		0.402
L2	22.80		23.20	0.898		0.913
L3	26.30		26.70	1.035		1.051
L4	43.20		44.40	1.701		1.748
L5	4.30		4.70	0.169		0.185
L6	24.30		24.70	0.957		0.972
L7	14.60		15.00	0.575		0.591
N	1.80		2.20	0.071		0.087
R	3.80		4.20	0.150		0.165
DIA	3.40		3.80	0.134		0.150



- Weight : 5.6 g (typ.)
- Maximum Torque (applied to mounting flange) Recommended: 0.55 Nm; Maximum: 1 Nm
- The side of the dissipator must be flat within 80 mm

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**ST2001FX**

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